



POWER SKY (H.K.) LTD.

Digital transistors (built-in resistors)

DTA144TE/ DTA144TUA/

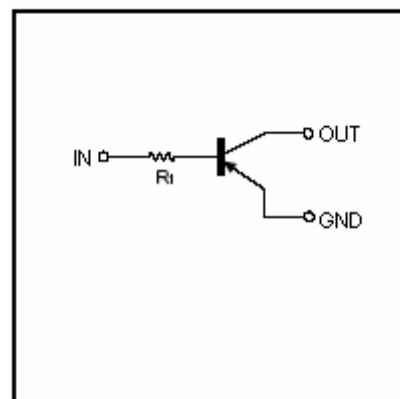
DTA144TCA/DTA144TKA/DTA144TSA

DIGITAL TRANSISTOR (PNP)

Features

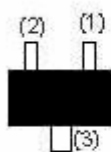
- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making device design easy.

●Equivalent circuit



PIN CONNENCTIONS AND MARKING

DTA144TE

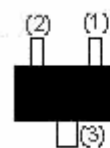


(1) IN
(2) GND
(3) OUT

SOT-523

Abbreviated symbol: 96

DTA144TUA

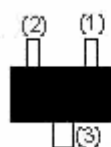


(1) IN
(2) GND
(3) OUT

SOT-323

Abbreviated symbol: 96

DTA144TKA

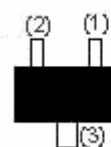


(1) IN
(2) GND
(3) OUT

SOT-23-3L

Abbreviated symbol: 96

DTA144TCA

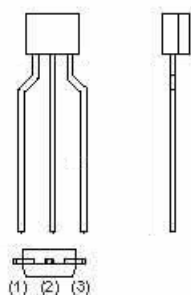


(1) IN
(2) GND
(3) OUT

SOT-23

Abbreviated symbol: 96

DTA144TSA



(1) GND
(2) OUT
(3) IN

TO-92S

MAXIMUM RATINGS* $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	LIMITS(DTA144T□)					Units
		E	UA	KA	CA	SA	
V _{CBO}	Collector-Base Voltage	-50					V
V _{CEO}	Collector-Emitter Voltage	-50					V
V _{EBO}	Emitter-Base Voltage	-5					V
I _C	Collector Current -Continuous	-100					mA
P _C	Collector Dissipation	150	200			300	mW
T _j	Junction temperature	150					°C
T _J , T _{stg}	Junction and Storage Temperature	-55~+150					°C

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-0.5	μA
DC current gain	h_{FE}	$V_{CE} = -5\text{V}, I_C = -1\text{mA}$	100	300	600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5\text{mA}, I_B = -0.5\text{mA}$			-0.3	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_E = 5\text{mA}, f = 100\text{MHz}$		250		MHz
Input resistor	R1		32.9	47	61.1	$k\Omega$

Typical Characteristics

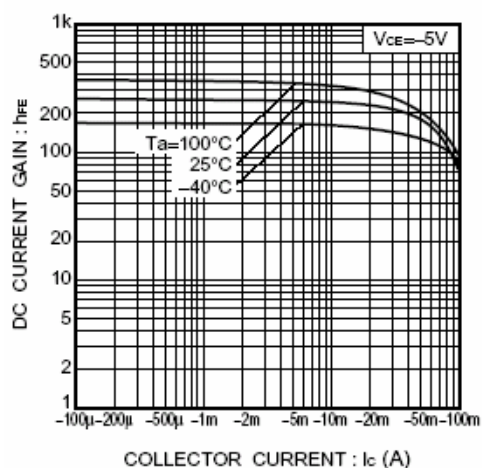


Fig.1 DC current gain vs.collector current

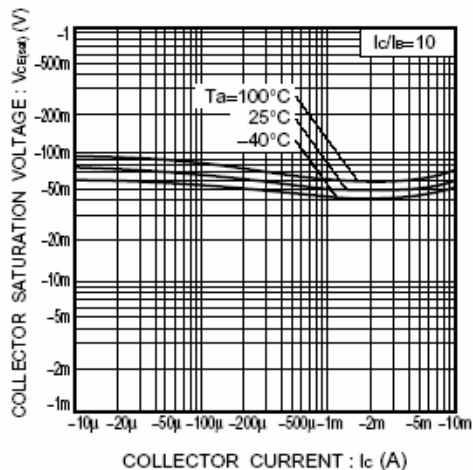


Fig.2 Collector-emitter saturation voltage vs.collector current